

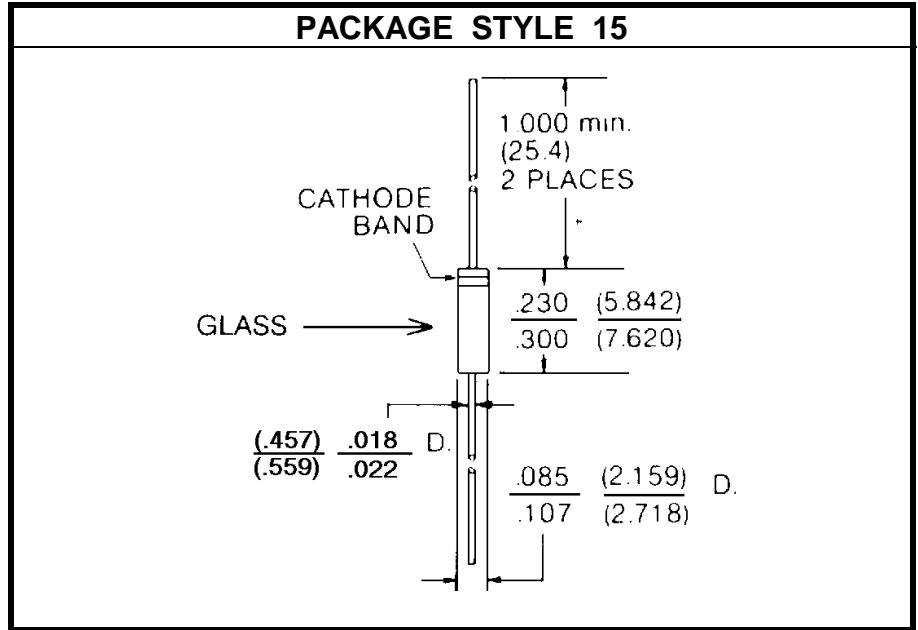
# SILICON PIN DIODE

**DESCRIPTION:**

The **AP1000A** is a Diffused Epitaxial Silicon PIN Diode.

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	100mA
<b>V<sub>CE</sub></b>	100 V
<b>P<sub>DISS</sub></b>	500 mW @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +150 °C
<b>T<sub>STG</sub></b>	-65 °C to +175 °C
<b>θ<sub>JC</sub></b>	50 °C/W
<b>T<sub>SOLD</sub></b>	5.0 Sec./200 °C


**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V <sub>B</sub>	I <sub>R</sub> = 10 μA	100			V
C <sub>J</sub>	V <sub>R</sub> = 6.0 V f = 1.0 MHz			0.05	pF
R <sub>S</sub>	I <sub>F</sub> = 20 mA I <sub>F</sub> = 100 mA f = 1.0 GHz			2.6 2.0	Ohms
T <sub>L</sub>	I <sub>F</sub> = 10 mA I <sub>R</sub> = 6.0 mA		100		nS
T <sub>S</sub>	10%-90% / 90%-10%			10	nS
C <sub>P</sub>	f = 1.0 MHz		0.15		pF
L <sub>S</sub>			2.5		nH